BUK9880-55A

N-channel TrenchMOS logic level FET

19 March 2014

Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources

3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	-	55	V
I _D	drain current	V _{GS} = 5 V; T _{sp} = 25 °C; <u>Fig. 3</u> ; <u>Fig. 2</u>	-	-	7	Α
P _{tot}	total power dissipation	T _{sp} = 25 °C; <u>Fig. 1</u>	-	-	8	W
Static characte	eristics					,
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 8 A; T_j = 25 °C	-	62	73	mΩ
		V_{GS} = 4.5 V; I_D = 8 A; T_j = 25 °C	-	-	89	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 8 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 13;$ Fig. 14	-	68	80	mΩ
Avalanche rug	gedness					,
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 6 A; $V_{sup} \le$ 55 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	36	mJ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	4	D I
2	D	drain		
3	S	source		G T T
4	D	drain	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	mbb076 S

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK9880-55A	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			
BUK9880-55A/CU	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9880-55A	988055A
BUK9880-55A/CU	988055

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	55	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω	-	55	V
V_{GS}	gate-source voltage		-15	15	V
P _{tot}	total power dissipation	T _{sp} = 25 °C; <u>Fig. 1</u>	-	8	W
I _D	drain current	T _{sp} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>	-	4	Α
		T _{sp} = 25 °C; V _{GS} = 5 V; <u>Fig. 3</u> ; <u>Fig. 2</u>	-	7	Α
I _{DM}	peak drain current	T_{sp} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3	-	30	Α

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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	150	°C
T _j	junction temperature			-55	150	°C
V_{GSM}	peak gate-source voltage	pulsed; t _p ≤ 50 μs		-15	15	V
Source-drai	in diode				'	
I _S	source current	T _{sp} = 25 °C		-	7	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{sp} = 25 \ ^{\circ}C$		-	30	Α
Avalanche r	ruggedness				'	
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 6 A; $V_{sup} \le$ 55 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	36	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy	Fig. 4	[1][2][3]	<u>4]</u>	-	J

- [1] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 150 °C.
- [3] Repetitive avalanche rating limited by an average junction temperature of 145 °C.
- [4] Refer to application note AN10273 for further information.

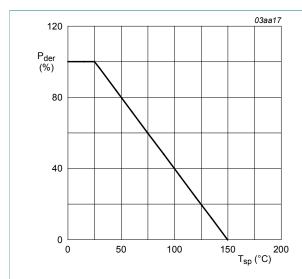


Fig. 1. Normalized total power dissipation as a function of solder point temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

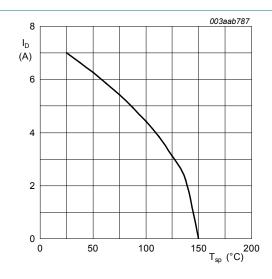


Fig. 2. Continuous drain current as a function of solder point temperature

$$V_{\rm GS} \geq 5\,V$$

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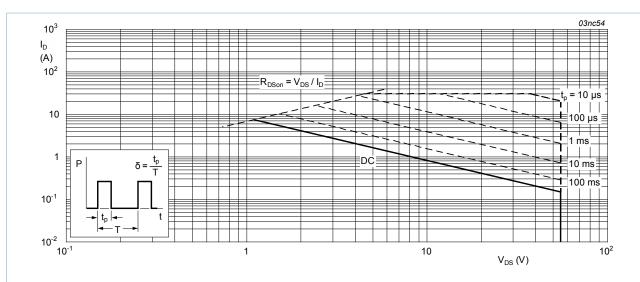


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$$T_{amb} = 25$$
° C ; I_{DM} is single pulse

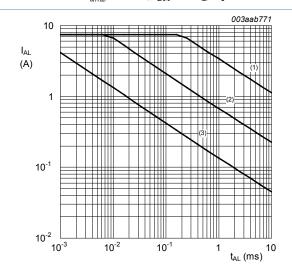


Fig. 4. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time.

(1) Single-pulse; $T_j = 25 \, {}^{\circ}C$.

(2) Single-pulse; $T_j = 125 \, ^{\circ}C$.

(3) Repetitive.

9. Thermal characteristics

Table 6. Thermal characteristics

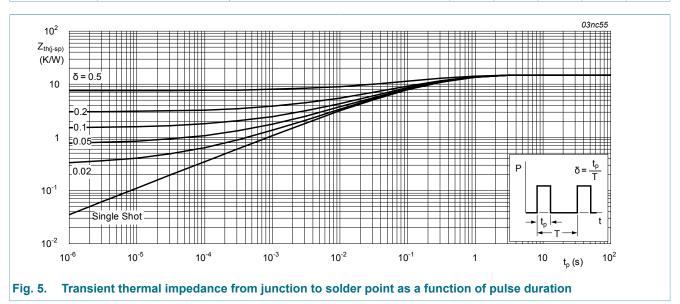
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	15	K/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 5	-	120	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 ^{\circ}\text{C}$	50	-	-	V
	breakdown voltage	I _D = 0.25 mA; V _{GS} = 0 V; T _j = 25 °C	55	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 12; Fig. 8	1	1.5	2	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 150 °C; Fig. 12; Fig. 8	0.6	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; Fig. 12; Fig. 8	-	-	2.3	V
I _{DSS}	drain leakage current	V _{DS} = 55 V; V _{GS} = 0 V; T _j = 150 °C	-	-	500	μA
		V _{DS} = 55 V; V _{GS} = 0 V; T _j = 25 °C	-	0.05	10	μΑ
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 8 A; T _j = 150 °C; Fig. 13; Fig. 14	-	-	147	mΩ
		V _{GS} = 10 V; I _D = 8 A; T _j = 25 °C	-	62	73	mΩ
		V _{GS} = 4.5 V; I _D = 8 A; T _j = 25 °C	-	-	89	mΩ
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _{GS} = 5 V; I _D = 8 A; T _j = 25 °C; <u>Fig. 13;</u> <u>Fig. 14</u>	-	68	80	mΩ
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	I _D = 10 A; V _{DS} = 44 V; V _{GS} = 5 V;	-	11	-	nC
Q_{GS}	gate-source charge	Fig. 11	-	1.6	-	nC
Q_GD	gate-drain charge	I _D = 10 A; V _{DS} = 44 V; V _{GS} = 5 V; Fig. 15	-	4.6	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. } 16}{\text{C}}$	-	438	584	pF
C _{oss}	output capacitance		-	87	104	pF
C _{rss}	reverse transfer capacitance		-	62	85	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	8	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 ^{\circ}C$	-	118	-	ns
t _{d(off)}	turn-off delay time		-	20	-	ns
t _f	fall time		-	32	-	ns
Source-dra	ain diode				1	
V _{SD}	source-drain voltage	I_S = 15 A; V_{GS} = 0 V; T_j = 25 °C; <u>Fig. 17</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs;	-	33	-	ns
Q _r	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	60	-	nC

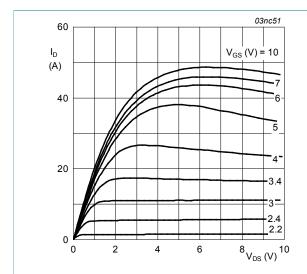


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values $T_j = 25 ^{\circ} C$

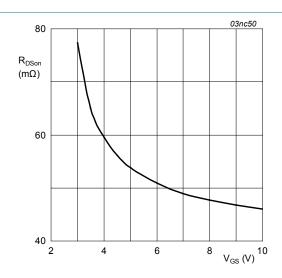


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 10A$$

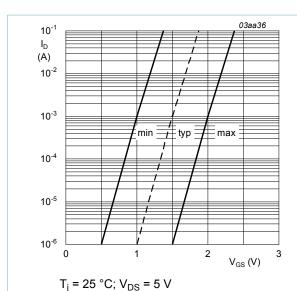


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

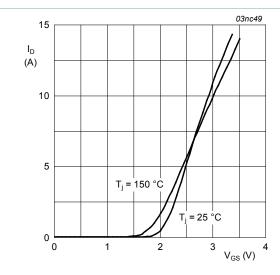


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} = 25V$$

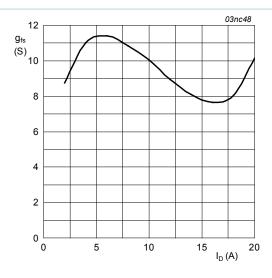


Fig. 9. Forward transconductance as a function of drain current; typical values

$$T_j=25^{\circ}C; V_{DS}=25V$$

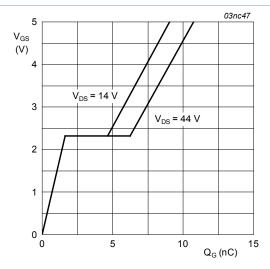


Fig. 11. Gate-source voltage as a function of turn-on gate charge; typical values

$$T_j=25^{\circ}C; I_D=10A$$

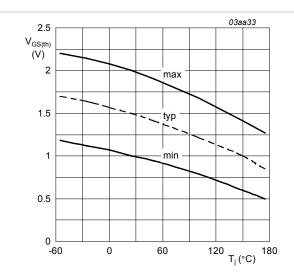


Fig. 12. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1mA; V_{DS} = V_{GS}$$

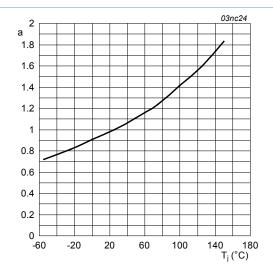


Fig. 14. Normalized drain source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

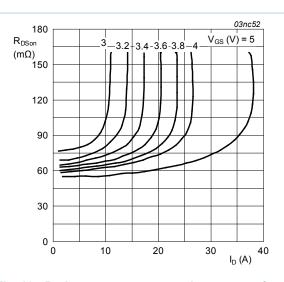


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C$$

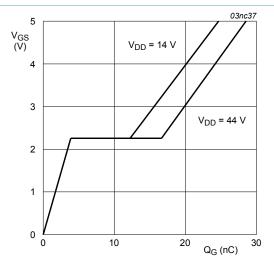


Fig. 15. Gate-source voltage as a function of turn-on gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 15A$$

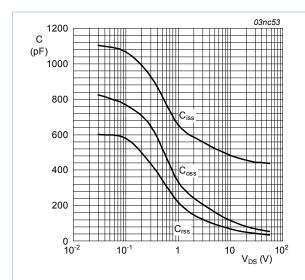
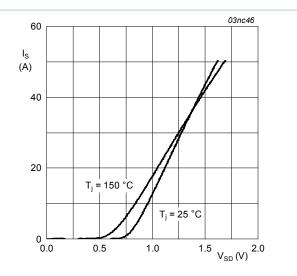


Fig. 16. Input, output and reverse transfer capacitances | Fig. 17. Reverse diode current as a function of reverse as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$



diode voltage; typical value

$$V_{GS} = 0V$$

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11. Package outline

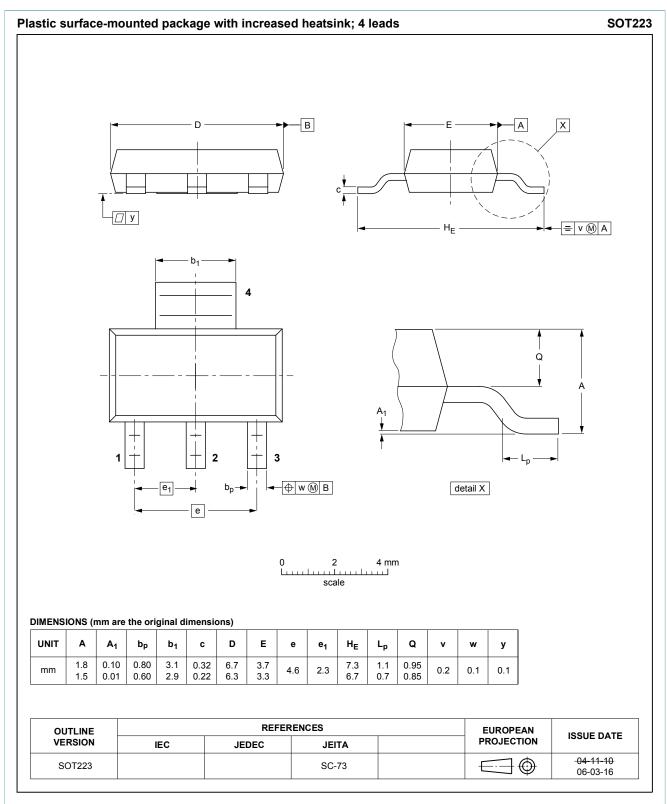


Fig. 18. Package outline SC-73 (SOT223)

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